AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A DFB type semiconductor laser device comprising:

a laser part including an active layer and a clad ~~layer,~~ layer;

a grating layer mounted on said clad layer and having periodic apertures; ~~,~~

an insulating layer mounted on said grating layer, ~~and an electrode layer laminated in order,~~ said ~~the~~ insulating layer including at least one elongated gap extending in a direction transverse to a grating of said ~~the~~ grating layer; and

a metal electrode layer mounted on said insulating layer so as to contact through said apertures of said grating layer with said clad layer within said gap ~~so that the electrode layer contacts the grating layer and the clad layer~~ .

2. (Previously Presented) The DFB type semiconductor laser device according to claim 1, wherein the active layer is composed of at least InGaAsP and the clad layer is composed of p-InP, and the grating layer is composed of InGaAs.

3. (Previously Presented) The DFB type semiconductor laser device according to claim 2, wherein the clad layer has a thickness equal to or thinner than 0.5 μm.

4. (Withdrawn) A method of manufacturing a DFB type semiconductor laser device, comprising the steps of forming a laser substrate including at least a waveguide layer and a clad layer; forming a grating layer on a top surface of the laser substrate; forming an insulating layer having at least one through groove extending to the grating layer in a direction in which a resonator of the laser device is formed; forming an electrode layer made of a high refractive material on the insulating layer; and forming a further electrode layer on a bottom surface of the laser substrate.

5. (Withdrawn) The method according to claim 4, wherein the step of forming the grating layer comprises the steps of forming a contact layer on the clad layer of the laser substrate, and removing a portion of the contact layer by lithography to form a plurality of parallel ridges aligning in parallel to one another in the direction in which the resonator of the laser device is formed.